

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

**Product Summary**

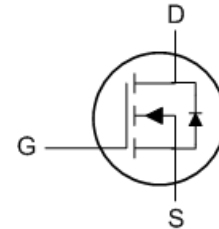
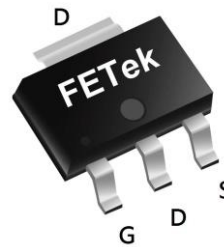


BVDSS	RDSON	ID
100V	75mΩ	3A

**Description**

The FKL0006 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The FKL0006 meets the RoHS and Green Product requirement with full function reliability approved.

**SOT223 Pin Configuration**



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	3	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	2.4	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	15	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	2	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	85	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	24	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	0.082	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	60	75	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	65	82	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.8	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	---	5.8	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.4	2.8	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	40	56	nC
Q <sub>gs</sub>	Gate-Source Charge		---	7.3	10.2	
Q <sub>gd</sub>	Gate-Drain Charge		---	7	9.8	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =3A	---	9.2	18.4	ns
T <sub>r</sub>	Rise Time		---	22	40	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	41	82	
T <sub>f</sub>	Fall Time		---	19.6	39	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2400	3360	pF
C <sub>oss</sub>	Output Capacitance		---	100	140	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	82	115	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	3	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	15	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =3A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	41	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	25	---	nC

Note :

 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3.The power dissipation is limited by 150°C junction temperature

 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

Typical Characteristics

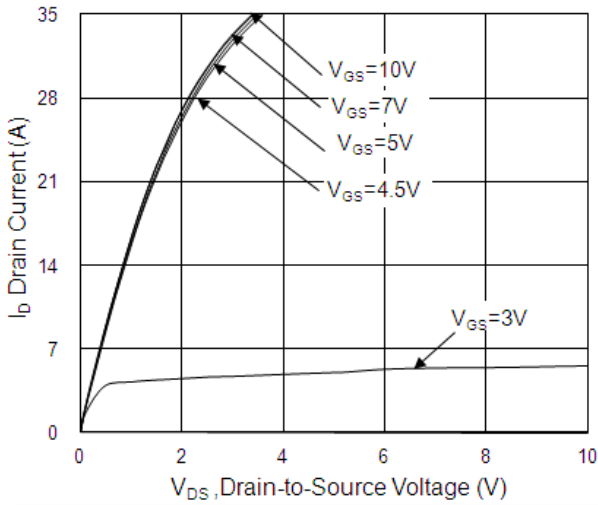


Fig.1 Typical Output Characteristics

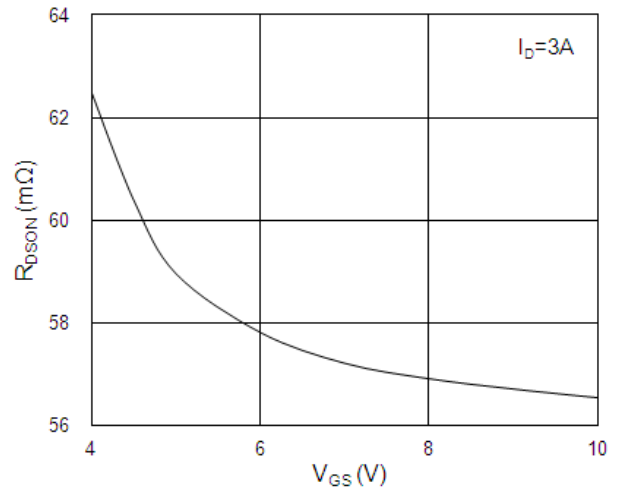


Fig.2 On-Resistance vs. Gate-Source

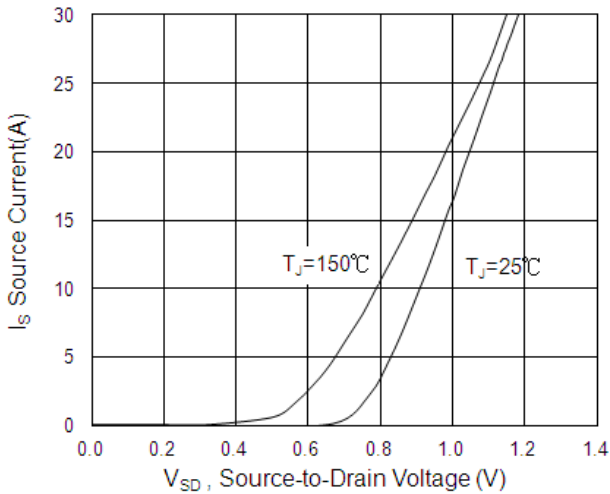


Fig.3 Forward Characteristics of Reverse

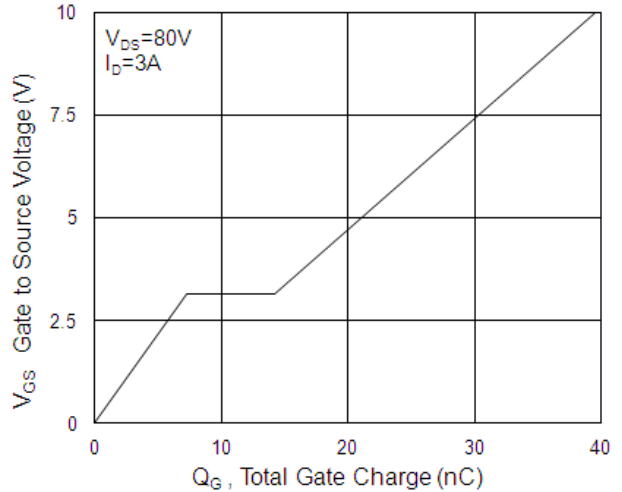


Fig.4 Gate-Charge Characteristics

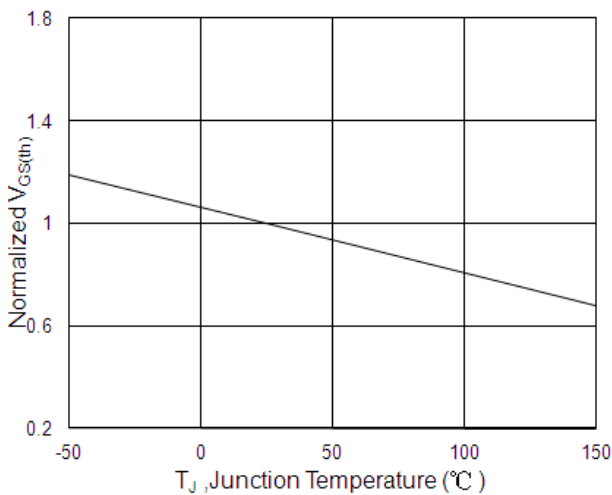


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

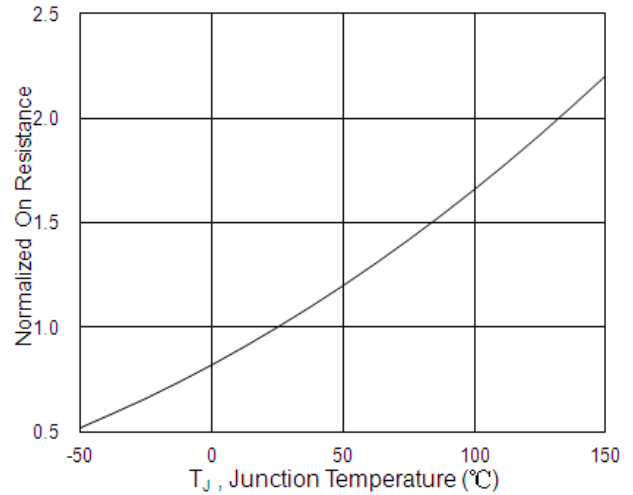


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

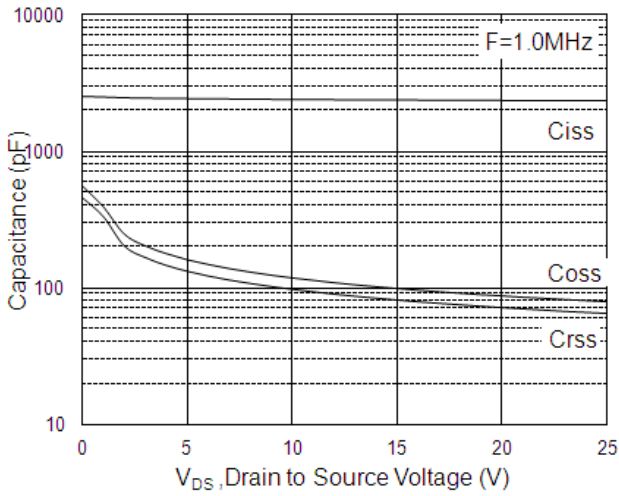


Fig.7 Capacitance

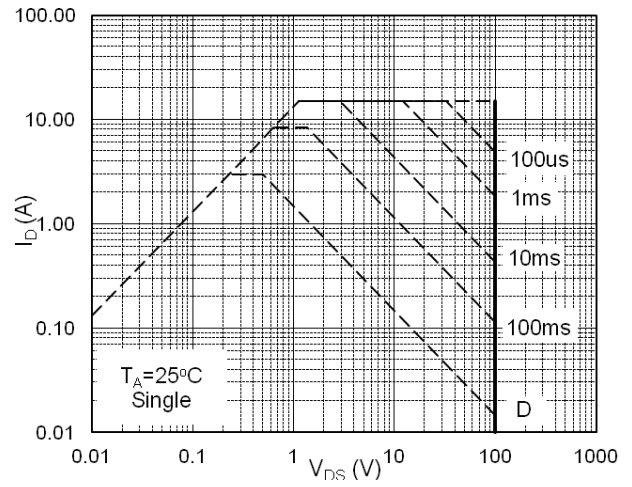


Fig.8 Safe Operating Area

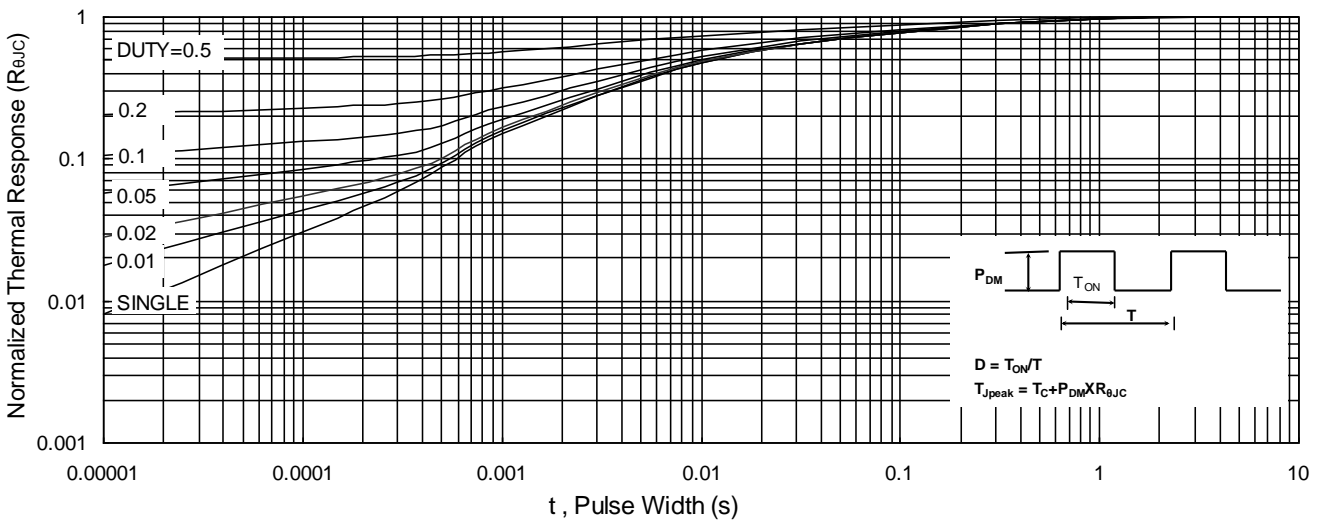


Fig.9 Normalized Maximum Transient Thermal Impedance

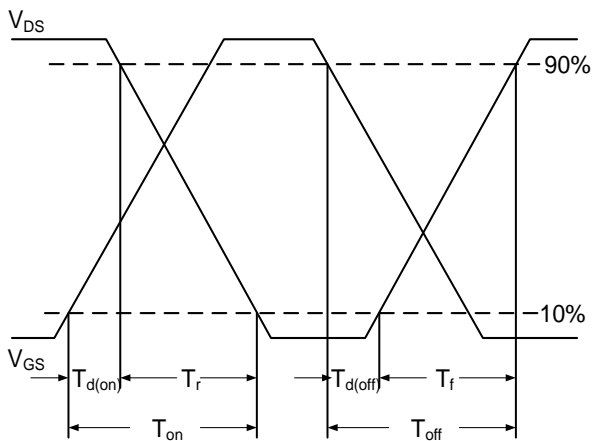


Fig.10 Switching Time Waveform

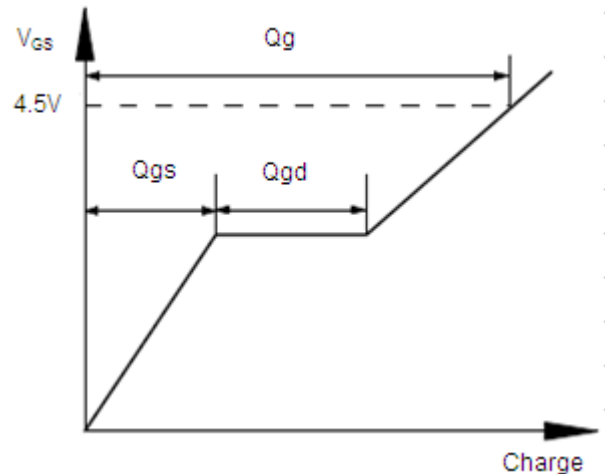


Fig.11 Gate Charge Waveform